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# Crystal Oscillator / Clock Generator with optional SSC

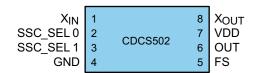
#### **FEATURES**

- Part of a Family of Easy to use Clock Generator Devices With Optional SSC
- Crystal Oscillator With Integrated Crystal Capacitors, Selectable Output Frequency and Selectable SSC
- SSC Controllable via 2 External Pins
   ±0%, ±0.5%, ±1%, ±2% Center Spread
- Frequency Multiplication Selectable Between x1 or x4 With one External Control Pin
- Single 3.3V Device Power Supply
- Wide Temperature Range –40°C to 85°C
- Low space Consumption by 8 pin TSSOP Package

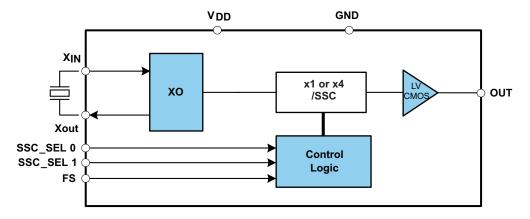
## **APPLICATIONS**

 Consumer and Industrial Applications requiring Crystal Oscillator with the possibility of EMI reduction through Spread Spectrum Clocking

#### **PACKAGE**



#### **BLOCK DIAGRAM**





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### DESCRIPTION

The CDCS502 is a spread spectrum capable, fundamental mode crystal oscillator with selectable frequency multiplication.

It features an advanced gain controlled fundamental mode crystal oscillator stage with a built-in load capacitance of 10pF. This oscillator stage accepts crystals from 8MHz to 32MHz with an ESR of up to  $180\Omega$ . The stage can be used with crystals with power dissipation of  $50\mu W$  and up.

The input signal is processed by a PLL, whose output frequency is either equal to the input frequency or multiplied by the factor of 4.

The PLL is also able to spread the clock signal by  $\pm 0\%$ ,  $\pm 0.5\%$ ,  $\pm 1\%$  or  $\pm 2\%$  centered around the output clock frequency with an triangular modulation.

By this, the device can generate output frequencies between 8MHz and 108MHz with or without SSC from a fundamental mode crystal.

In x1 Mode with an SSC amount of 0%, the device works as a standard crystal oscillator and does not make use of the built in PLL.

The CDCS502 operates in 3.3V environment.

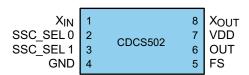
It is characterized for operation from -40°C to 85°C. It is offered in an 8 Pin TSSOP package.

#### **FUNCTION TABLE**

FS	SSC_SEL 0	SSC_SEL 1	SSC Amount	f <sub>OUT</sub> /f <sub>IN</sub>	f <sub>OUT</sub> at f <sub>in</sub> = 27 MHz
0	0	0	±0.00%	1	27 MHz <sup>(1)</sup>
0	0	1	±0.50%	1	27 MHz
0	1	0	±1.00%	1	27 MHz
0	1	1	±2.00%	1	27 MHz
1	0	0	±0.00%	4	108 MHz
1	0	1	±0.50%	4	108 MHz
1	1	0	±1.00%	4	108 MHz
1	1	1	±2.00%	4	108 MHz

<sup>(1)</sup> In this mode the signal from the crystal bypasses the internal PLL for maximum performance.

#### **PACKAGE**



#### **PIN FUNCTIONS**

SIGNAL	PIN	TYPE	DESCRIPTION
X <sub>IN</sub>	1	1	Crystal Input
X <sub>OUT</sub>	8	0	Crystal Output
OUT	6	0	LVCMOS Clock Output
SSC_SEL 0, 1	2, 3	1	Spread Selection Pins, internal pull-up
FS	5	1	Frequency Multiplication Selection, internal pull-up
$V_{DD}$	7	Power	3.3V Power Supply
GND	4	Ground	Ground

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## PACKAGE THERMAL RESISTANCE FOR TSSOP (PW) PACKAGE<sup>(1)</sup>

	CDCV204DW 9 DIN TCCOD		THI	ERMAL AIF	R FLOW (C	FM)	UNIT
	CDCV304PW 8-PIN TSSOP	0	150	250	500	UNII	
$R_{\theta JA}$	High K		149	142	138	132	°C/W
$R_{\theta JA}$	Low K		230	185	170	150	°C/W
$R_{\theta JC}$	High K	65					°C/W
$R_{\theta JC}$	High K	69					°C/W

<sup>(1)</sup> The package thermal impedance is calculated in accordance with JESD 51 and JEDEC2S2P (high-k board).

## **ABSOLUTE MAXIMUM RATINGS**(1)

over operating free-air temperature range (unless otherwise noted)

		VALUE	UNIT
$V_{DD}$	Supply voltage range	-0.5 to 4.6	V
V <sub>IN</sub>	Input voltage range	-0.5 to 4.6	V
V <sub>out</sub>	Output voltage range	-0.5 to 4.6	V
I <sub>IN</sub>	Input current $(V_1 < 0, V_1 > VDD)$	±20	mA
l <sub>out</sub>	Continuous output current	±50	mA
T <sub>ST</sub>	Storage temperature range	-65 to 150	°C
$T_{J}$	Maximum junction temperature	125	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
$V_{DD}$	Supply voltage	3.0		3.6	V
f <sub>IN</sub>	Input Frequency	8		32	MHz
V <sub>IL</sub>	Low level input voltage LVCMOS			0.3 VDD	V
V <sub>IH</sub>	High level input voltage LVCMOS	0.7 VDD			V
VI	Input Voltage threshold LVCMOS		0.5 VDD		V
C <sub>L</sub>	Output Test Load LVCMOS			10	pF
I <sub>OH</sub> /I <sub>OL</sub>	Output Current			12	mA
T <sub>A</sub>	Operating free-air temperature	-40		85	°C

## RECOMMENDED CRYSTAL SPECIFICATIONS(1)

	PARAMETER	CONDITIONS	MIN	NOM	MAX	UNIT
f <sub>X-tal</sub>	Om retal in much fire museum and man	FS = 0	8		32	NAL I—
	Crystal input frequency range	FS = 1	8		27	MHz
ESR	Effective series resistance (2)				180	Ω
C <sub>L</sub>	On-chip load capacitance at Xin and Xout			10		pF
T <sub>X-tal</sub>	Crystal power dissipation		50			μW

<sup>(1)</sup> For further details on the crystal, see the crystal part in the Applications section

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<sup>(2)</sup> With 5 pF crystal package parallel capacitance



## **DEVICE CHARACTERISTICS**

over operating free-air temperature range (unless otherwise noted)

PARAMET ER		CONDITIONS	MIN	TYP	MAX	UNIT
		f <sub>out</sub> = 20 MHz; FS = 0, no SSC		8		
IDD	Device supply current	f <sub>out</sub> = 20 MHz; FS = 0, SSC = 2%		18		mA
		f <sub>out</sub> = 70 MHz; FS = 1, SSC = 2%		22		
4	Output fraguage	FS = 0	8		32	MHz
f <sub>OUT</sub>	Output frequency	FS = 1	32		108	MHz
I <sub>IH</sub>	LVCMOS input current	V <sub>I</sub> = VDD; VDD = 3.6 V			10	μΑ
I <sub>IL</sub>	LVCMOS input current	V <sub>I</sub> = 0 V; VDD = 3.6 V			-10	μΑ
		$I_{OH} = -0.1 \text{ mA}$	2.9			
$V_{OH}$	LVCMOS high-level output voltage	I <sub>OH</sub> = - 8 mA	2.4			V
	voitago	$I_{OH} = -12 \text{ mA}$	2.2			
		$I_{OL} = 0.1 \text{ mA}$			0.1	
$V_{OL}$	LVCMOS low-level output voltage	I <sub>OL</sub> = 8 mA			0.5	V
	voltago	I <sub>OL</sub> = 12 mA			0.8	
t <sub>jit(CC)</sub>	Cycle to cycle jitter	f <sub>out</sub> = 108 MHz; FS = 1, SSC = 1%, 10000 Cycles		100		ps
t <sub>r</sub> /t <sub>f</sub>	Rise and fall time	20%–80%		0.75		ns
O <sub>dc</sub>	Output duty cycle	PLL active	45%		55%	
f <sub>MOD</sub>	Modulation frequency			30		kHz

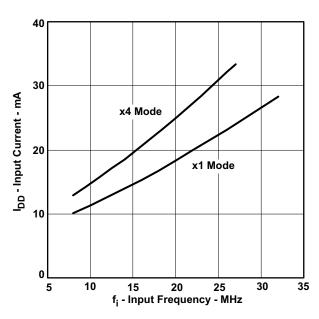


Figure 1. IDD vs Input Frequency, VCC = 3.3V, SSC = 2%

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Figure 2. Phase Noise Plot, x1 Mode, 0% SSC, 27 MHz Crystal

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#### **APPLICATION INFORMATION**

#### **SELECTION OF A CRYSTAL**

The CDCS502 requires a crystal with a frequency between 8 and 32 MHz (27MHz in x4 Mode). The crystal stage is designed with an internal load capacitance of 10pF for crystals with this shunt load capacitance. If a slightly bigger capacity then 10pF is needed, small external capacitors can be used to get to this value. This solution however might influence the power-up behavior of the crystal stage, so using a 10pF load capacitance crystal is highly recommended.

For further details on capacitive load calculation, see application report (SCAA085).

#### NOTE:

Even though the CDCS502 is characterized down to  $-40^{\circ}$ C, a standard crystal is usually not rated for operation at this low temperature.

#### SSC MODULATION

The exact implementation of the SSC modulation plays a vital role for the EMI reduction. The CDCS502 uses a triangular modulation scheme implemented in a way that the modulation frequency depends on the VCO frequency of the internal PLL and the spread amount is independent from the VCO frequency.

The modulation frequency can be calculated by using one of the below formulas chosen by frequency multiplication mode.

FS =0:  $f_{mod} = f_{IN} / 708$ FS =1:  $f_{mod} = f_{IN} / 620$ 

#### PARAMETER MEASUREMENT INFORMATION

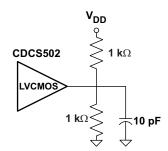


Figure 3. Test Load

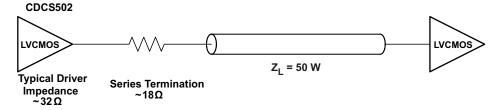


Figure 4. Test Load for  $50-\Omega$  Board Environment

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## PACKAGE OPTION ADDENDUM

10-Dec-2020

#### **PACKAGING INFORMATION**

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Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CDCS502PW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CS502	Samples
CDCS502PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CS502	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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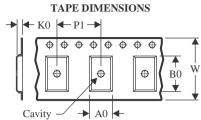
10-Dec-2020

# **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCS502PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

# **PACKAGE MATERIALS INFORMATION**

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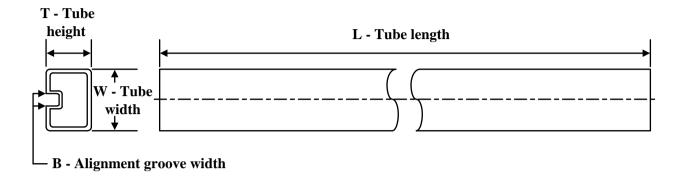
## \*All dimensions are nominal

Devic	Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CDCS502	PWR	TSSOP	PW	8	2000	356.0	356.0	35.0	

# **PACKAGE MATERIALS INFORMATION**

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## **TUBE**

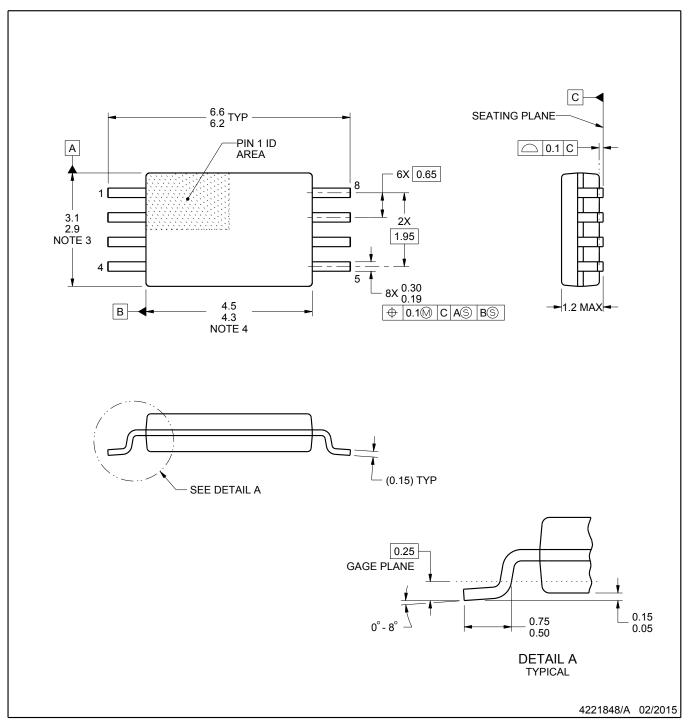


### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CDCS502PW	PW	TSSOP	8	150	530	10.2	3600	3.5



SMALL OUTLINE PACKAGE



## NOTES:

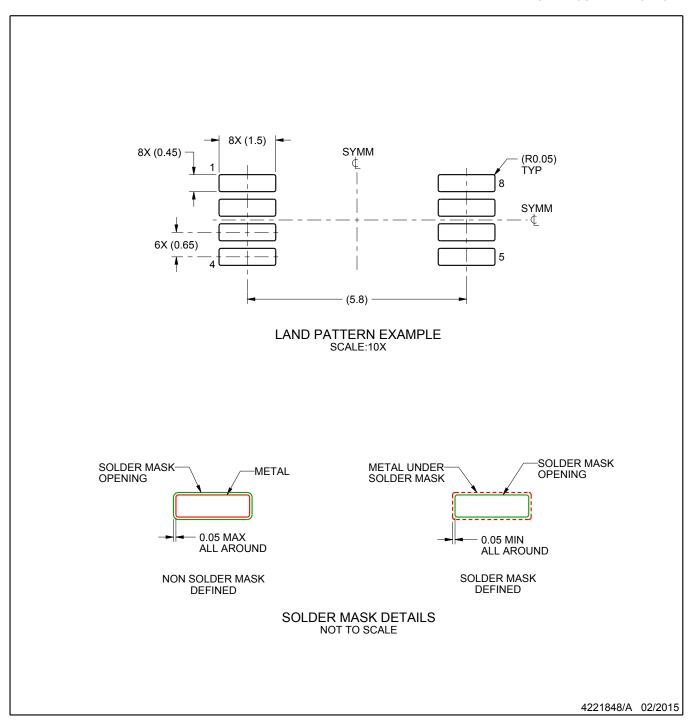
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



SMALL OUTLINE PACKAGE



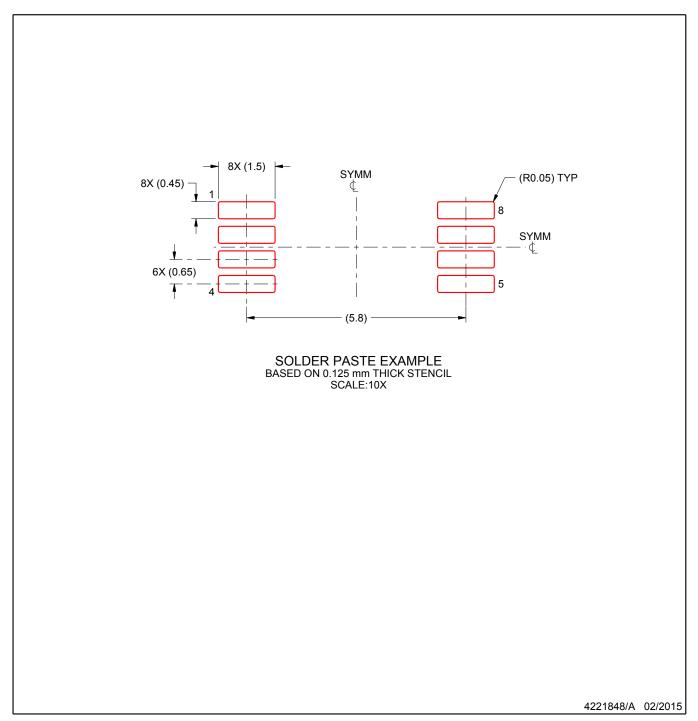
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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